

# GO-GaN<sup>®</sup>

## MOSFETs for Power Electronics

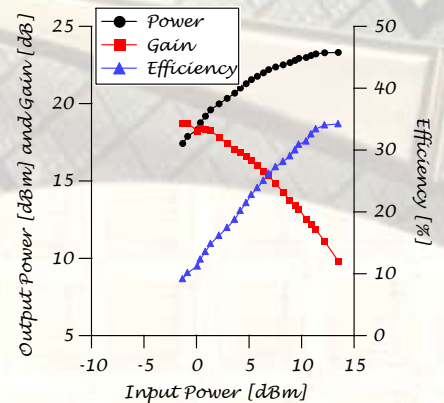
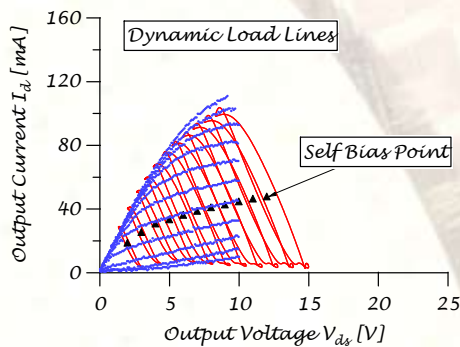
The 'O' in **OSEMI** is for Gate-Oxide. We have had GaN and GaAs-based MOSFET materials and devices in development for many years. We are pleased to offer these Patented devices to qualified customers. The Compound Semiconductor MOSFET promises higher performance and increased integration levels. The high breakdown voltage and excellent performance of the GaN MOSFETs make them particularly suitable for a variety of cutting edge power electronics applications. We would be pleased to work with you on your device or circuit requirements. Please contact **OSEMI** to discuss Compound Semiconductor MOSFETs.

### Epitaxy Integration Strength in Combination



### Advantages of Gate-Oxides and Compound Semiconductor MOSFETs:

- Passivation of Surface States
- Low Microwave Dispersion
- Higher Power Density Devices
- Low noise figures (NF)
- No Field Plate needed on Gate
- Planar process technology
- Improved Breakdown Voltage
- Smaller die size when compared with standard HFETs
- High yields
- Good lifetime
- Reasonable cost



OSEMI is an ARPE-e finalist for Power Electronics using our patented **GO-GaN<sup>®</sup>** Technology.

